

Pb Free Plating Product

MURB1020CTR/MURB1030CTR/MURB1040CTR/MURB1060CTR



10.0 Ampere Surface Mount Dual Common Anode Ultra Fast Recovery Rectifiers

Features

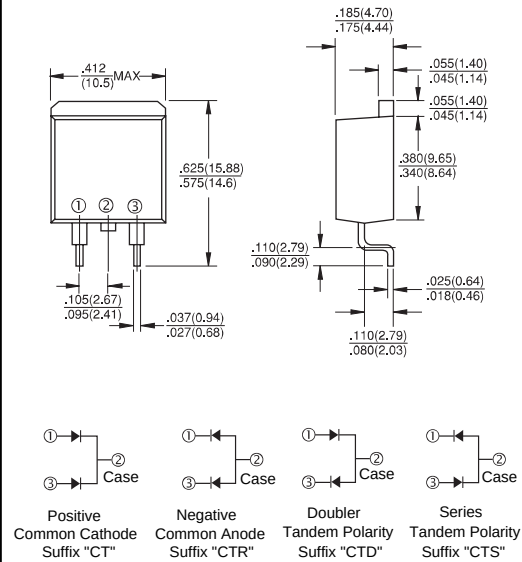
- ★ Latest GPP EPI P/G Technology
- ★ Good Soft Recovery Characteristics
- ★ Ideally Suited for Automatic Assembly
- ★ Low Forward Voltage
- ★ High Surge Current Capability
- ★ Low Leakage Current

Applications

- ★ Freewheeling, Snubber, Clamp
- ★ Inversion Welder
- ★ PFC
- ★ Plating Power Supply
- ★ Ultrasonic Cleaner and Welder
- ★ Converter & Chopper
- ★ UPS/LED SMPS/HID

D2PAK/TO-263

Unit : inch (mm)

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	MURB1020CTR	MURB1030CTR	MURB1040CTR	MURB1060CTR	Unit
Peak Repetitive Reverse Voltage	V _{RRM}	200	300	400	600	V
Working Peak Reverse Voltage	V _{RWM}					
DC Blocking Voltage	V _R					
RMS Reverse Voltage	V _{R(RMS)}	140	210	280	420	V
Average Rectified Output Current @T _C = 100°C	I _O	10.0 5.0				A
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load (JEDEC Method)	I _{FSM}	100				A
Forward Voltage per diode @I _F = 5.0A	V _{FM}	0.98	1.3	1.7		V
Peak Reverse Current At Rated DC Blocking Voltage @T _C = 25°C @T _C = 100°C	I _{RM}	5.0 100				μA
Reverse Recovery Time (Note 1)	t _r	35	50			nS
Typical Junction Capacitance (Note 2)	C _J	70	50			pF
Thermal Resistance Junction to Ambient (Note 3)	R _{θJA}	30				°C/W
Thermal Resistance Junction to Lead (Note 3)	R _{θJC}	1.5				
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150				°C

Note: 1. Measured with I_F = 0.5A, I_R = 1.0A, I_{RR} = 0.25A.
 2. Measured at 1.0 MHz and applied reverse voltage of 4.0 V DC.
 3. Mounted on PCB with minimum recommended pad sizes per diode.

RATINGS AND CHARACTERISTICS CURVES

(T_A=25°C unless otherwise noted)